ABSTRACT OF THE DISCLOSURE

A high electron mobility transistor comprises a GaN-based electron accumulation layer formed on a substrate, an electron supply layer formed on the electron accumulation layer, a source electrode and a drain electrode formed on the electron supply layer and spaced from each other, a gate electrode formed on the electron supply layer between the source and drain electrodes, and a hole absorption electrode formed on the electron accumulation layer so as to be substantially spaced from the electron supply layer. Since the hole absorption electrode is formed on the electron absorption layer in order to prevent holes generated by impact ionization from being accumulated on the electron accumulation layer, a kink phenomenon is prevented. Good drain-current/voltage characteristics are therefore obtained. A high power/high electron mobility transistor is provided with a high power-added efficiency and good linearity.